

AMENDMENTS TO THE CLAIMS:

Please cancel Claims 1 through 7, 10, and 11 without prejudice to or disclaimer of the subject matter recited therein.

Please amend Claims 8 and 9 as follows:

1-7. (Cancelled)

8. (Currently Amended) ~~The method according to claim 1;~~ A method for manufacturing a semiconductor apparatus device including a plurality of layers on a semiconductor substrate, said method comprising the steps of:

dividing a pattern of at least a layer into a plurality of sub-patterns; and

joining the divided sub-patterns to perform patterning,

wherein as to a layer including wiring substantially affecting operation of the semiconductor device depending on a positional relationship to any other wiring, the patterning is performed by one-shot exposure using a single mask,

wherein only as to the layer including the wiring substantially affecting the operation of the semiconductor device depending on the positional relationship to any other wiring, the patterning is performed by one-shot exposure, and as to all of the other layers, the patterning is performed by division exposure.

9. (Currently Amended) ~~The method according to claim 1,~~ A method for manufacturing a semiconductor apparatus device including a plurality of layers on a semiconductor substrate, said method comprising the steps of:

dividing a pattern of at least a layer into a plurality of sub-patterns; and

joining the divided sub-patterns to perform patterning,

wherein as to a layer including wiring substantially affecting operation of the semiconductor device depending on a positional relationship to any other wiring, the patterning is performed by one-shot exposure using a single mask,

wherein as to layers to be patterned prior to the patterning of the layer including the wiring substantially affecting the operation of the semiconductor device depending on positional relationship to any other wiring, the patterning is performed by one-shot exposure, and as to all of the other layers to be patterned after the one-shot exposure, the patterning is performed by division exposure.

10-11. (Cancelled)